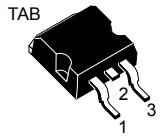
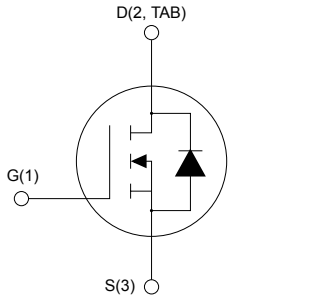
N-channel 650 V, 85 mΩ typ., 27 A MDmesh M5 Power MOSFET in a D²PAK package



D²PAK



Features

Order code	V_{DS}	$R_{DS(on)}$ max.	I_D
STB35N65M5	650 V	98 mΩ	27 A

- Higher V_{DSS} rating
- Higher dv/dt capability
- Excellent switching performance
- Extremely low $R_{DS(on)}$
- 100% avalanche tested

Applications

- Switching applications

Description

This device is an N-channel Power MOSFET based on the MDmesh M5 innovative vertical process technology combined with the well-known PowerMESH horizontal layout. The resulting product offers extremely low on-resistance, making it particularly suitable for applications requiring high power and superior efficiency.

Product status link
STB35N65M5

Product summary	
Order code	STB35N65M5
Marking	35N65M5
Package	D²PAK
Packing	Tape and reel

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	±25	V
I_D	Drain current (continuous) at T_C = 25 °C	27	A
I_D	Drain current (continuous) at T_C = 100 °C	17	A
I_{DM}(1)	Drain current (pulsed)	108	A
P_{TOT}	Total power dissipation at T_C = 25 °C	160	W
dv/dt(2)	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature range	-55 to 150	°C
T_J	Maximum operating junction temperature	150	°C

1. *Pulse width limited by safe operating area.*
2. *I_{SD} ≤ 27 A, di/dt ≤ 400 A/µs; V_{DS} (peak) < $V_{(BR)DSS}$.*

Table 2. Thermal data

Symbol	Parameter	Value	Unit
R_{thJC}	Thermal resistance, junction-to-case	0.78	°C/W
R_{thJA}(1)	Thermal resistance, junction-to-ambient	30	°C/W

1. *When mounted on a standard 1 inch^2 area of FR-4 PCB with 2-oz copper.*

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_J max.)	9	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	800	mJ

2 Electrical characteristics

T_C = 25 °C unless otherwise specified.

Table 4. On/off states

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0 V	650	-	-	V
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 650 V	-	-	1	µA
		V_{GS} = 0 V, V_{DS} = 650 V, T_C = 125 °C(1)	-	-	100	µA
I_{GSS}	Gate body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V	-	-	±100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 13.5 A	-	85	98	mΩ

1. *Specified by design, not tested in production.*

Table 5. Dynamic

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{DS} = 100 V, f = 1 MHz, V_{GS} = 0 V	-	3750	-	pF
C_{oss}	Output capacitance		-	84	-	
C_{rss}	Reverse transfer capacitance		-	5.5	-	
$C_{o(tr)}$(1)	Equivalent output capacitance time related	V_{DS} = 0 to 520 V, V_{GS} = 0 V	-	220	-	pF
$C_{o(er)}$(2)	Equivalent output capacitance energy related		-	75	-	pF
R_g	Gate input resistance	f = 1 MHz open drain	-	1.6	-	Ω
Q_g	Total gate charge	V_{DD} = 520 V, I_D = 13.5 A, V_{GS} = 0 to 10 V (see the Figure 15. Test circuit for gate charge behavior)	-	83	-	nC
Q_{gs}	Gate-source charge		-	19	-	
Q_{gd}	Gate-drain charge		-	35	-	

1. *$C_{o(tr)}$ is an equivalent capacitance that provides the same charging time as Coss while V_{DS} is rising from 0 V to the stated value.*
2. *$C_{o(er)}$ is an equivalent capacitance that provides the same stored energy as C_{oss} while V_{DS} is rising from 0 V to the stated value.*

Table 6. Switching times

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
$t_{d(off)}$	Turn-off delay time	V_{DD} = 400 V, I_D = 16 A, R_G = 4.7 Ω, V_{GS} = 10 V (see the Figure 16. Test circuit for inductive load switching and diode recovery times and Figure 19. Switching time waveform)	-	60	-	ns
$t_{r(v)}$	Voltage rise time		-	12	-	
$t_{c(off)}$	Crossing time off		-	28	-	
$t_{f(i)}$	Current fall time		-	16	-	

Table 7. Source-drain diode

Symbol	Parameter	Test condition	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-	-	27	A
I_{SDM}(1)	Source-drain current (pulsed)		-	-	108	
V_{SD}(2)	Forward on voltage	I_{SD} = 27 A, V_{GS} = 0 V	-	-	1.5	V
t_{rr}	Reverse recovery time	I_{SD} = 27 A, di/dt = 100 A/µs V_{DD} = 60 V (see the Figure 16. Test circuit for inductive load switching and diode recovery times)	-	360	-	ns
Q_{rr}	Reverse recovery charge		-	7	-	µC
I_{RRM}	Reverse recovery current		-	36	-	A
t_{rr}	Reverse recovery time	I_{SD} = 27 A, di/dt = 100 A/µs V_{DD} = 60 V, T_J = 150 °C (see the Figure 16. Test circuit for inductive load switching and diode recovery times)	-	425	-	ns
Q_{rr}	Reverse recovery charge		-	8	-	µC
I_{RRM}	Reverse recovery current		-	38	-	A

1. *Pulse width limited by safe operating area.*
2. *Pulsed: pulse duration = 300 µs, duty cycle 1.5%.*

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

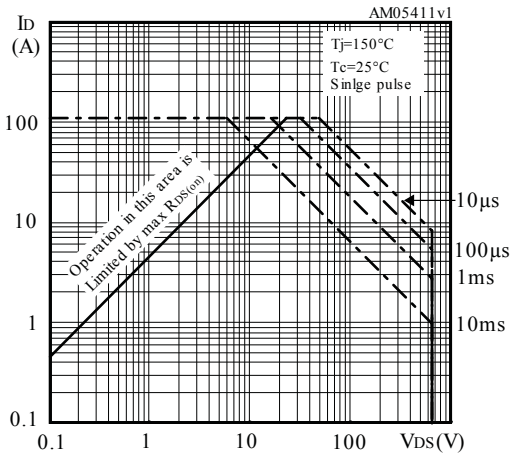


Figure 2. Normalized transient thermal impedance

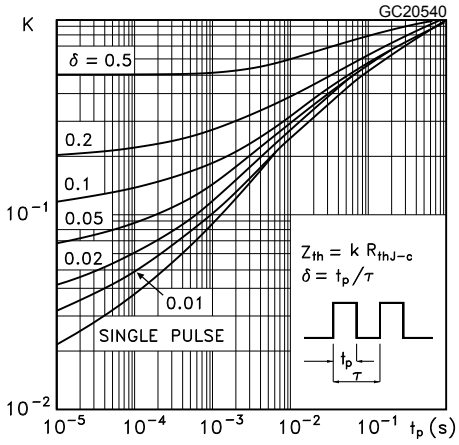


Figure 3. Output characteristics

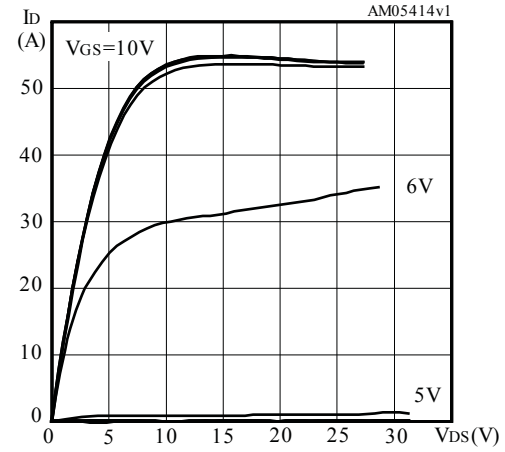


Figure 4. Transfer characteristics

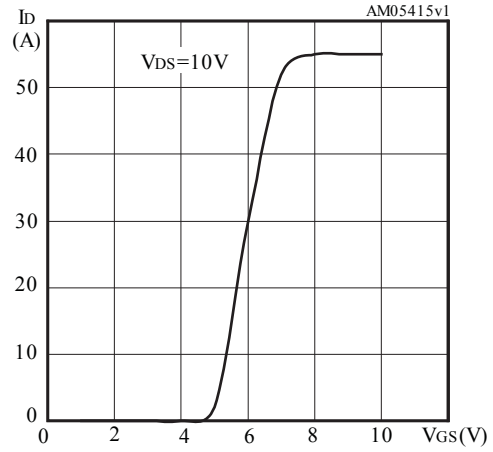


Figure 5. Gate charge vs gate-source voltage

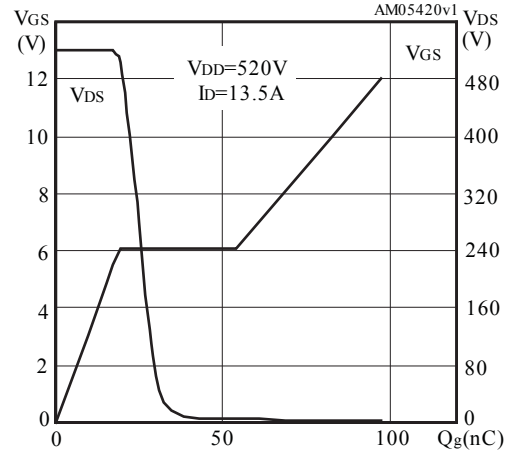


Figure 6. Static drain-source on-resistance

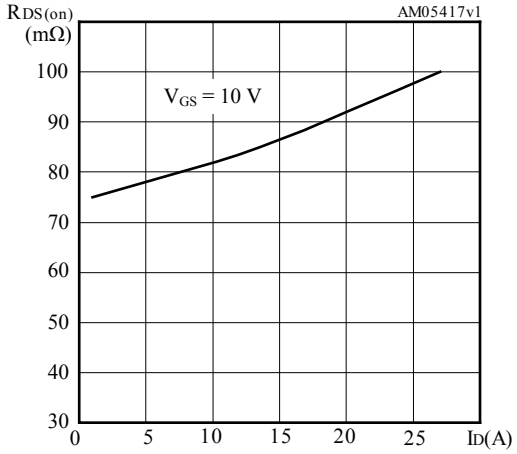


Figure 7. Capacitance variations

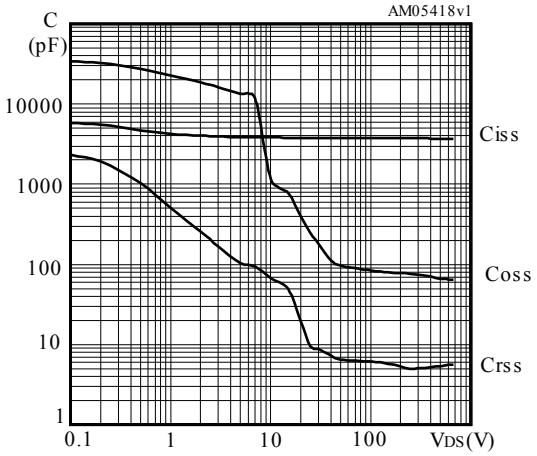


Figure 8. Output capacitance stored energy

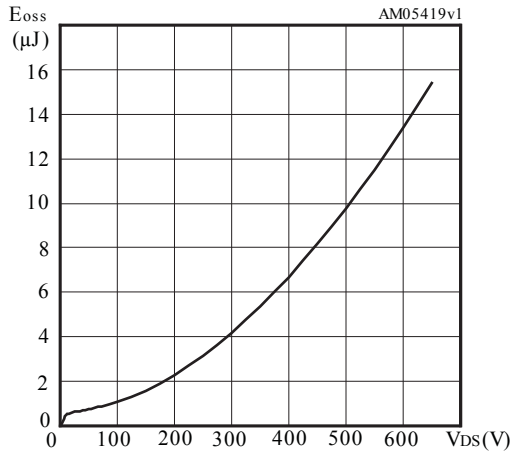


Figure 9. Normalized gate threshold voltage vs temperature

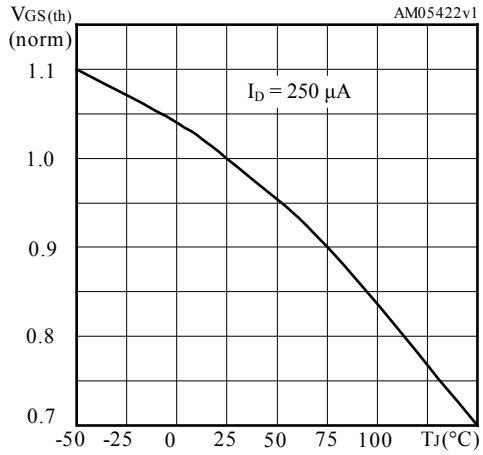


Figure 10. Normalized on-resistance vs temperature

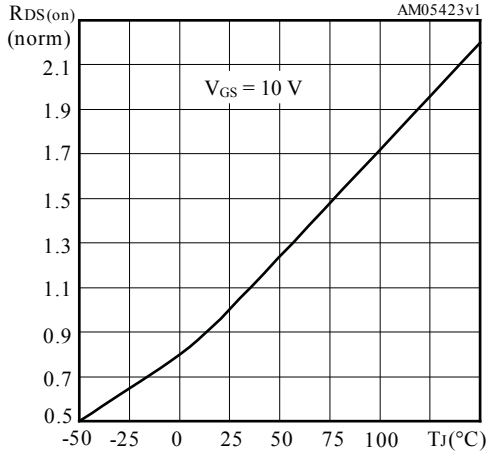


Figure 11. Drain-source diode forward characteristics

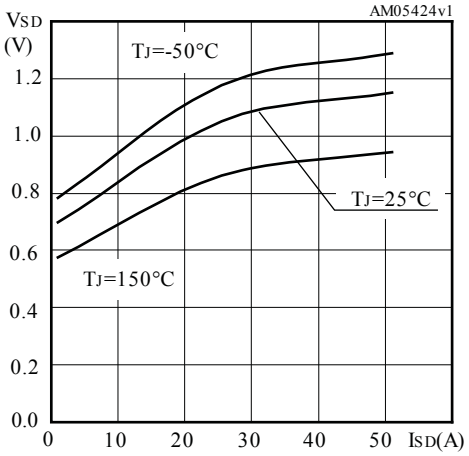


Figure 12. Normalized $V_{(BR)DSS}$ vs temperature

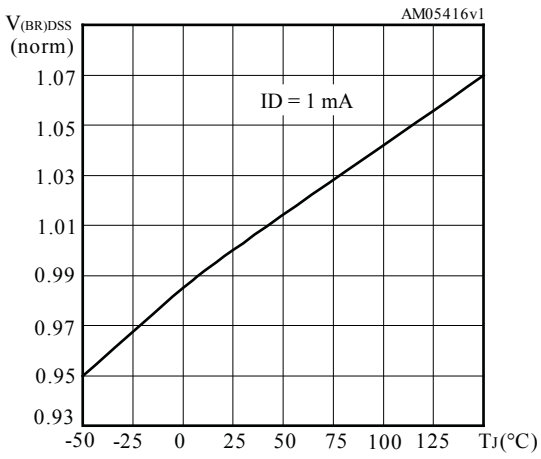
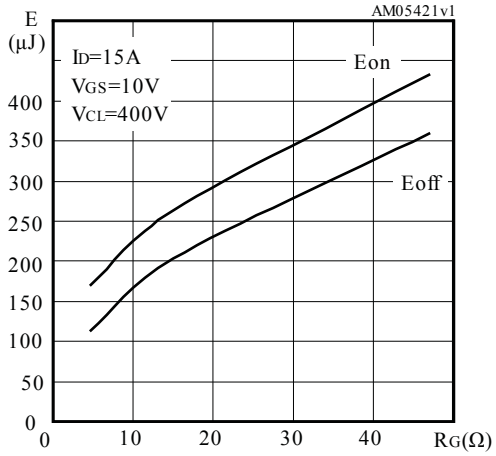


Figure 13. Switching energy vs gate resistance



Note: E_{on} including reverse recovery of a SiC diode.

3 Test circuits

Figure 14. Test circuit for resistive load switching times

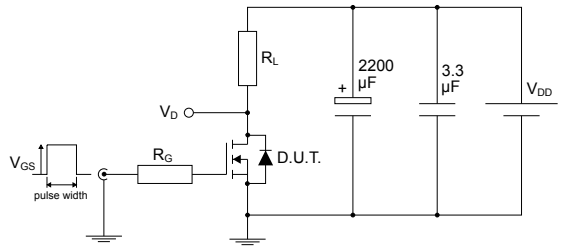


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Figure 15. Test circuit for gate charge behavior

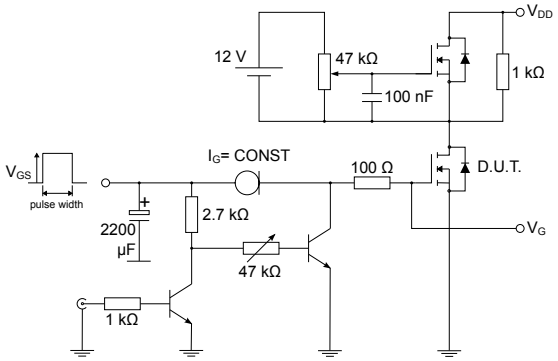

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Figure 16. Test circuit for inductive load switching and diode recovery times

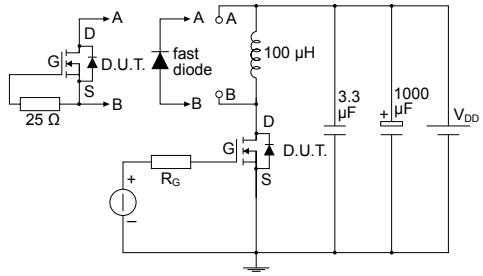

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Figure 17. Unclamped inductive load test circuit

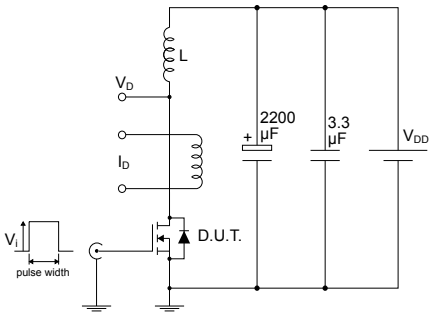

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Figure 18. Unclamped inductive waveform

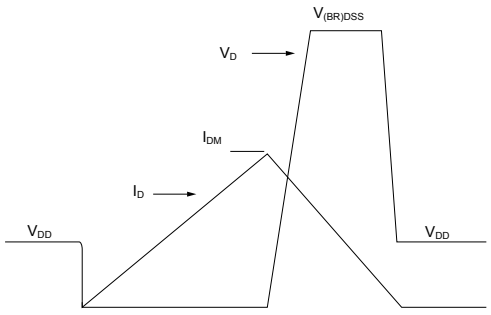

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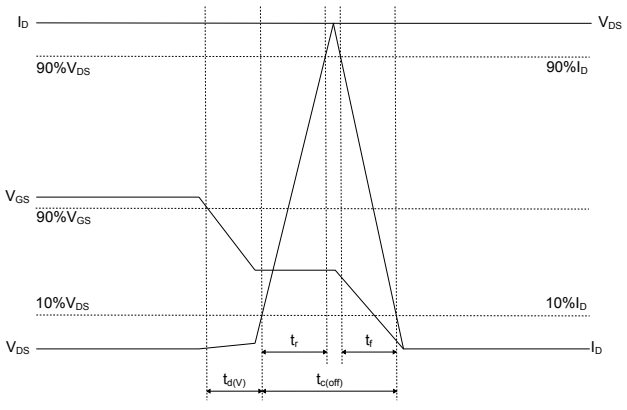
Figure 19. Switching time waveform



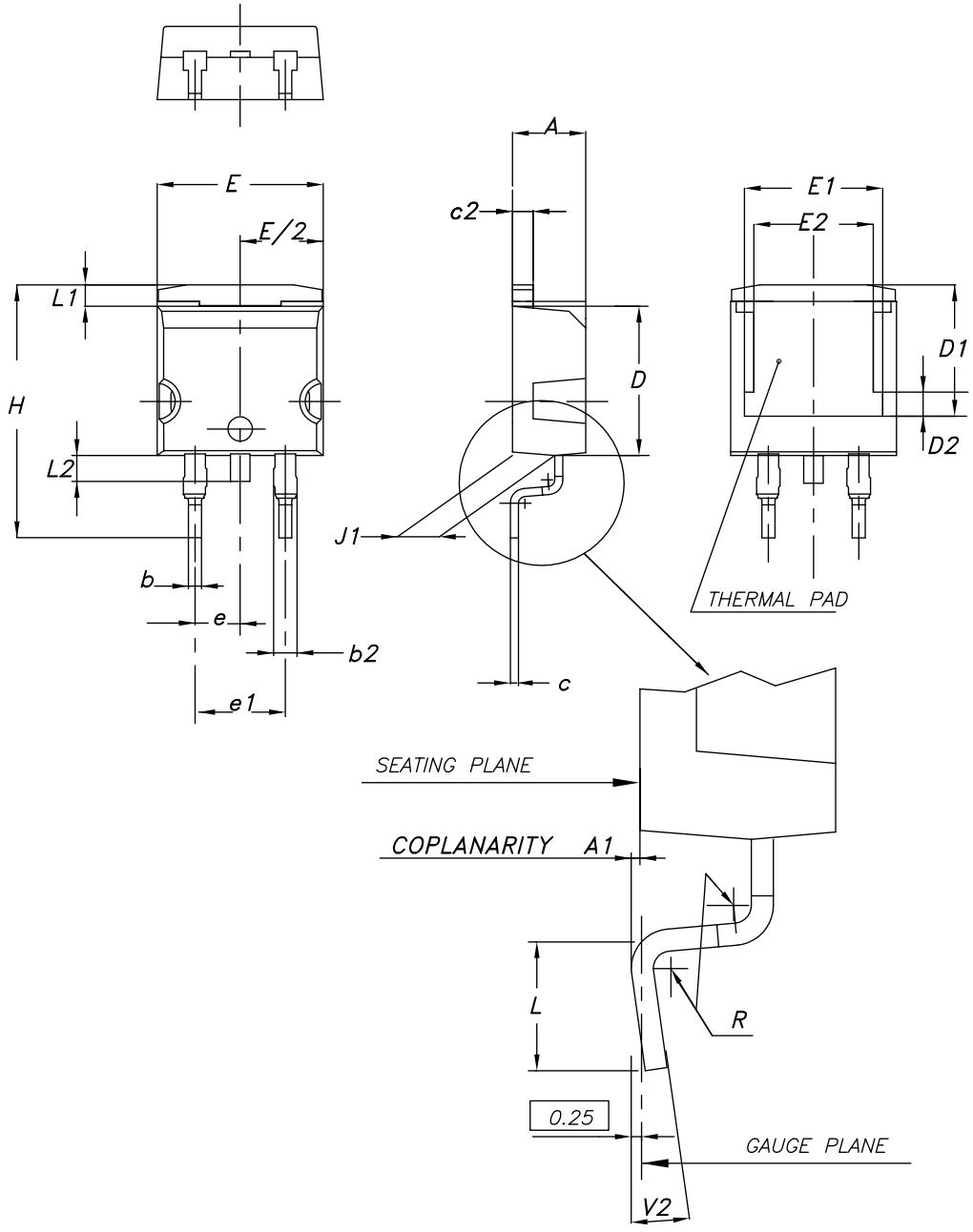
AM05540v2

4 Package information

To meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions, and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 D²PAK (TO-263) type A2 package information

Figure 20. **D²PAK (TO-263) type A2 package outline**

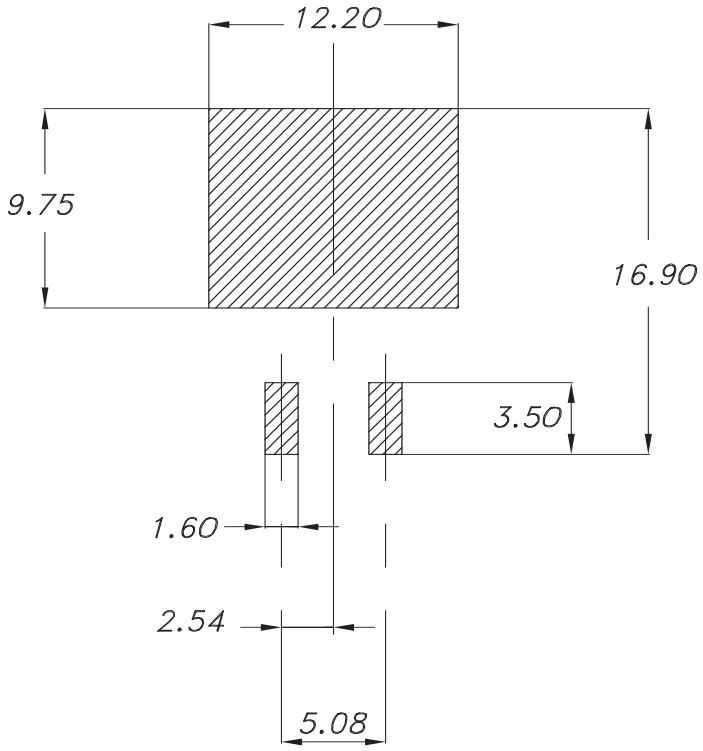


0079457_A2_27

Table 8. D²PAK (TO-263) type A2 package mechanical data

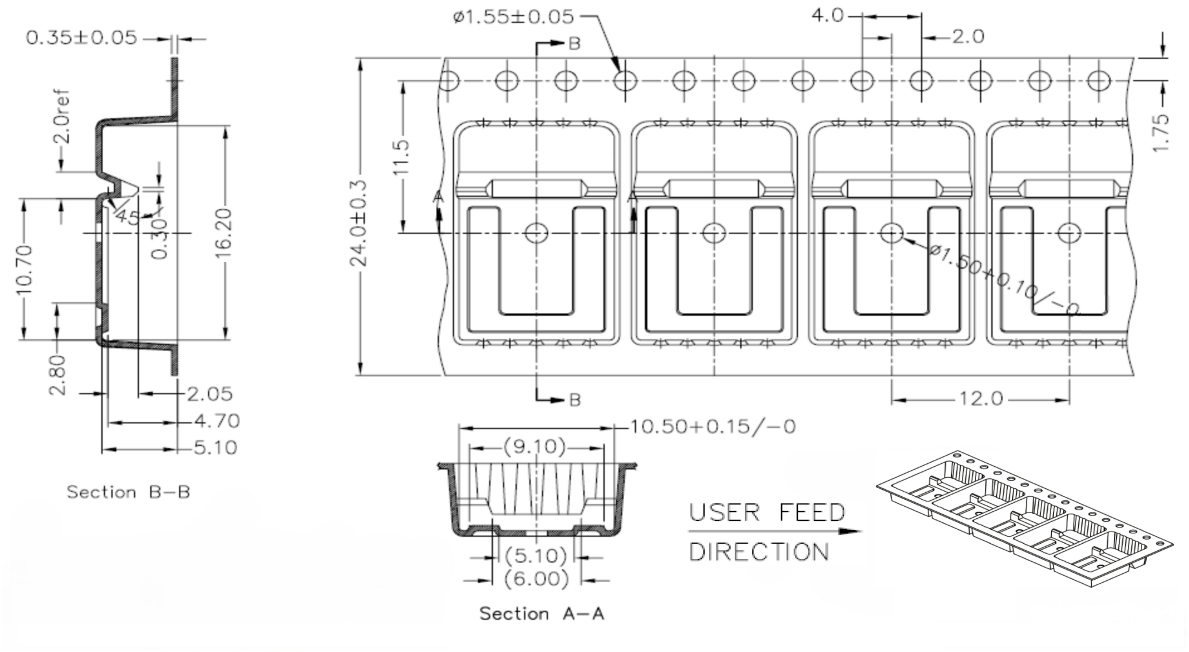
Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50	7.75	8.00
D2	1.10	1.30	1.50
E	10.00		10.40
E1	8.70	8.90	9.10
E2	7.30	7.50	7.70
e		2.54	
e1	4.88		5.28
H	15.00		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.40	
V2	0°		8°

Figure 21. D²PAK (TO-263) recommended footprint (dimensions are in mm)



4.2 D²PAK packing information

Figure 22. **D²PAK tape drawing (dimensions are in mm)**



Revision history

Table 9. **Document revision history**

Date	Revision	Changes
29-Jul-2009	1	First release.
01-Sep-2009	2	*Figure 10* has been updated.
06-Oct-2011	3	$C_{o(er)}$ and $C_{o(tr)}$ values changed in *Table 5: Dynamic*. *Table 6: Switching times* parameters updates. *Figure 24: Switching time waveform* has been corrected. Minor text changes. *Section 4: Package mechanical data* has been modified. Added: *Table 8: D²PAK (TO-263) mechanical data*, *Figure 25: D²PAK (TO-263) drawing* and *Figure 26: D²PAK footprint*; *Table 9: TO-220FP mechanical data* and *Figure 27: TO-220FP drawing*; *Table 10: I²PAK (TO-262) mechanical data* and *Figure 28: I²PAK (TO-262) drawing*; *Table 11: TO-220 type A mechanical data* and *Figure 29: TO-220 type A drawing*; *Table 12: TO-247 mechanical data* and *Figure 30: TO-247 drawing*; *Section 5: Packaging mechanical data* has been modified. Added: *Table 13: D²PAK (TO-263) tape and reel mechanical data*, *Figure 31: Tape* and *Figure 32: Reel*.
22-Sep-2025	4	Removed order code STF35N65M5, STI35N65M5, STP35N65M5 and STW35N65M5. Updated Section 4: Package information. Minor text changes.

Contents

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